



Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
150V	413mΩ@10V	1A

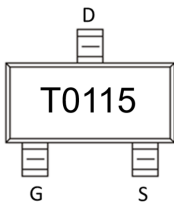
Feature

- Split Gate Trench Technology
- Low $R_{DS(ON)}$
- Low Gate Charge

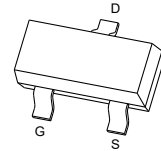
Application

- Power Switching Application

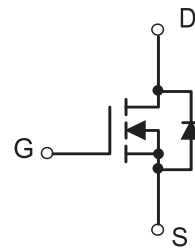
MARKING:



SOT-23



Schematic diagram



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	V_{DS}	150	V
Gate - Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^{1,5}	I_D	1	A
Pulsed Drain Current ²	I_{DM}	4	A
Power Dissipation ^{4,5}	P_D	0.4	mW
Thermal Resistance from Junction to Ambient ⁵	$R_{\theta JA}$	312	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$

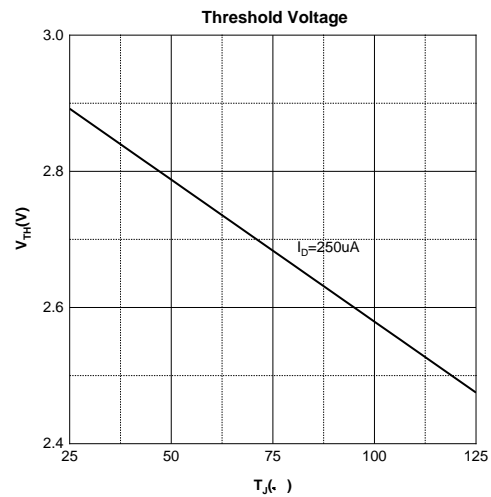
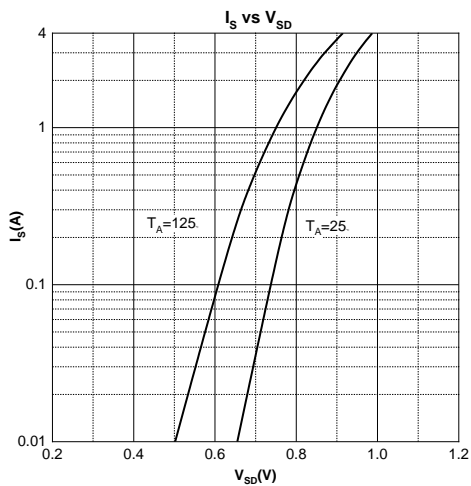
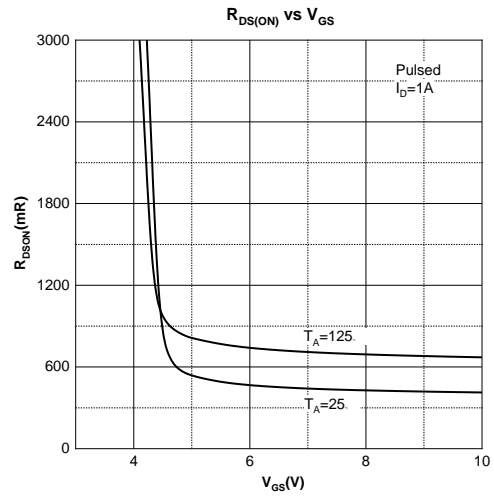
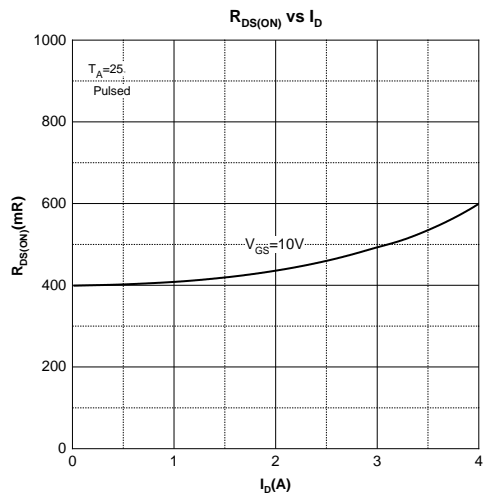
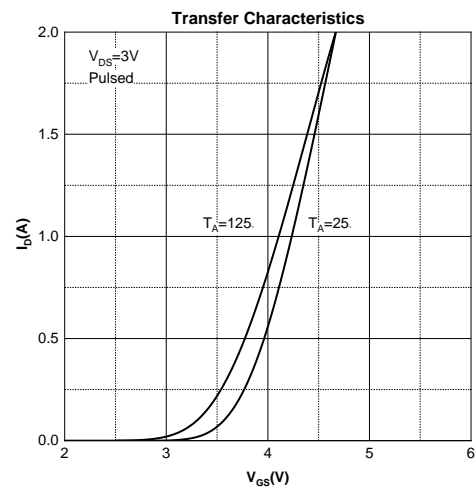
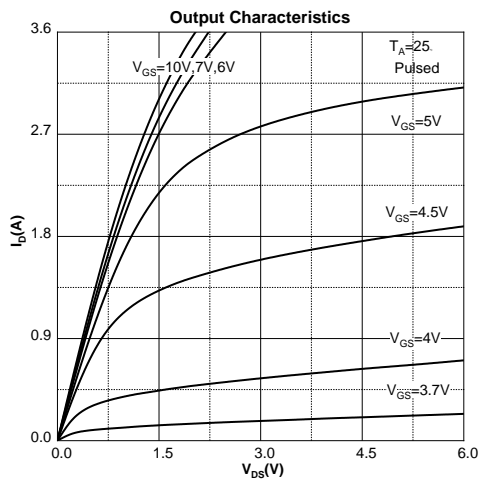
MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	150			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 150V, V_{GS} = 0V$			1	μA
Gate - Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
On Characteristics³						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2	2.9	4	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 1A$		413	650	m Ω
Dynamic Characteristics⁴						
Input Capacitance	C_{iss}	$V_{DS} = 75V, V_{GS} = 0V, f = 1MHz$		115		pF
Output Capacitance	C_{oss}			15		
Reverse Transfer Capacitance	C_{rss}			5		
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		1.8		Ω
Switching Characteristics⁴						
Total Gate Charge	Q_g	$V_{DS} = 75V, V_{GS} = 10V, I_D = 1.2A$		3.7		nC
Gate-source Charge	Q_{gs}			0.7		
Gate-drain Charge	Q_{gd}			1.7		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 75V, V_{GS} = 10V, R_L = 75\Omega, R_G = 3\Omega$		8		ns
Turn-on Rise Time	t_r			22		
Turn-off Delay Time	$t_{d(off)}$			9		
Turn-off Fall Time	t_f			20		
Source - Drain Diode Characteristics						
Diode Forward Voltage ³	V_{SD}	$V_{GS} = 0V, I_S = 1A$			1.2	V

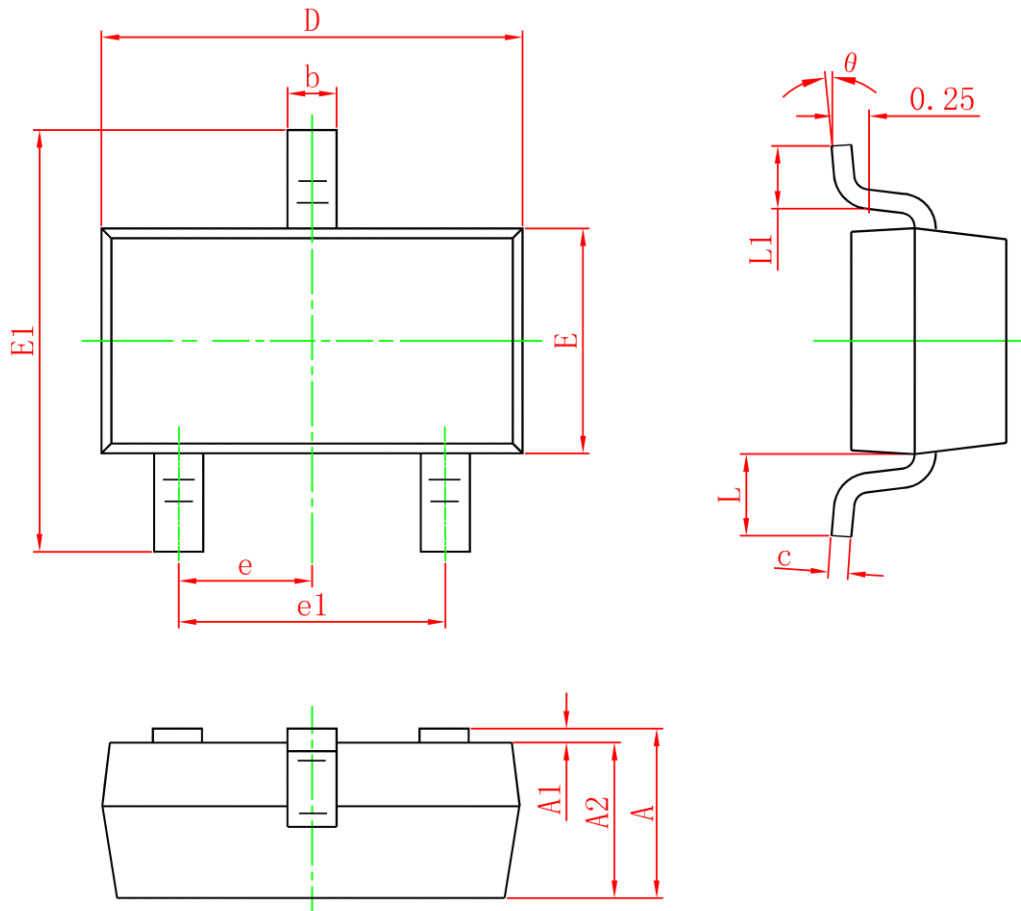
Notes :

- 1.The maximum current rating is limited by package.
- 2.Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
- 3.Pulse Test : Pulse Width $\leq 1500\mu s$, duty cycle $\leq 2\%$.
- 4.The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ\text{C}$.
- 5.Device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

Typical Characteristics



SOT-23 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0	0.100	0	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.150	1.500	0.045	0.059
E1	2.250	2.650	0.089	0.104
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°